

【Abstract】

The present invention relates to an etching composition and a method for manufacturing a semiconductor device using same. The etching composition comprises an inorganic acid and a silanol-based compound wherein the content of the silanol-based compound in the etching composition and the viscosity of the etching composition satisfy Equation 1, whereby the composition can secure a sufficient etch selectivity of a nitride film with respect to an oxide film while suppressing abnormal growth even in a high-temperature wet etching process, prevent the generation of bubbles immediately after production thus causing neither a decrease in the efficiency of the etching process nor damage to etching equipment, and exhibit excellent processability due to low viscosity.

Fig. 1